

Heterogeneous Integration: 2D - 3D Interconnects

2023 Chapter

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2023 Chapter Contributors

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Chapter Objectives

- Define and proliferate a standardized nomenclature for package architectures covering and clearly identifying, 2D and 3D and hybrid packaging constructs
 - Comprehend all HI announcements including Wafer-scale constructions.
- Define and disseminate key metrics driving the evolution of the physical interconnects in these architectures
 - The chapter lists their current values and projections for the next generations
- Chapter is organized into 4 primary areas:
 - Converged Nomenclature Framework for 2D , 3D and hybrid Architectures
 - Key Metrics:
 - Design Attributes
 - Electrical Attributes including Signaling and Power Delivery
 - Challenges
 - Discussion

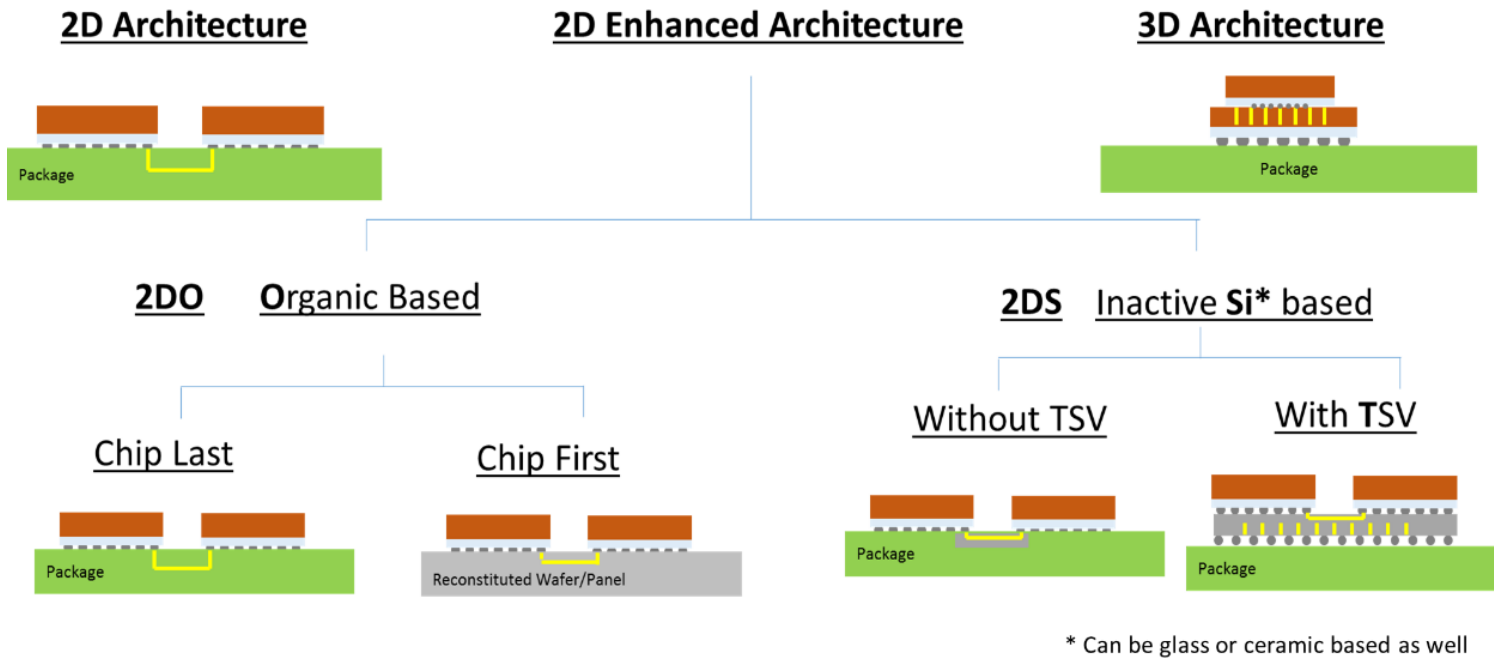
2023 Chapter Key Summary

- Nomenclature from a few years ago holds for the most part but will need an update (Thanks to Prof Fukushima & Venky for highlighting this). Mid-Year refresh proposed
- WB section is weak and needs help from experts like Jan Vardaman, Ivy Qin and Adeel Bajwa
- AI/ML driven increases in compute demand are forcing some non-linearity in our estimates and to respond, the BW roadmap has been expanded
- Lots of publications on standardized D2D links have appeared and references are updated to be fair to all and historically consistent
- Tom Gregorich made an excellent suggestion to define an interconnect landscape. It is a good idea but will need careful thought and argues for a mid-year update
- Table 5 on architecture-process elicited some good feedback. Have requested Dishit Parekh, Vidya Jayaram, Krutikesh Sahoo, Jan Vardaman and Adeel Bajwa to help get this table updated and correct.

Interconnects

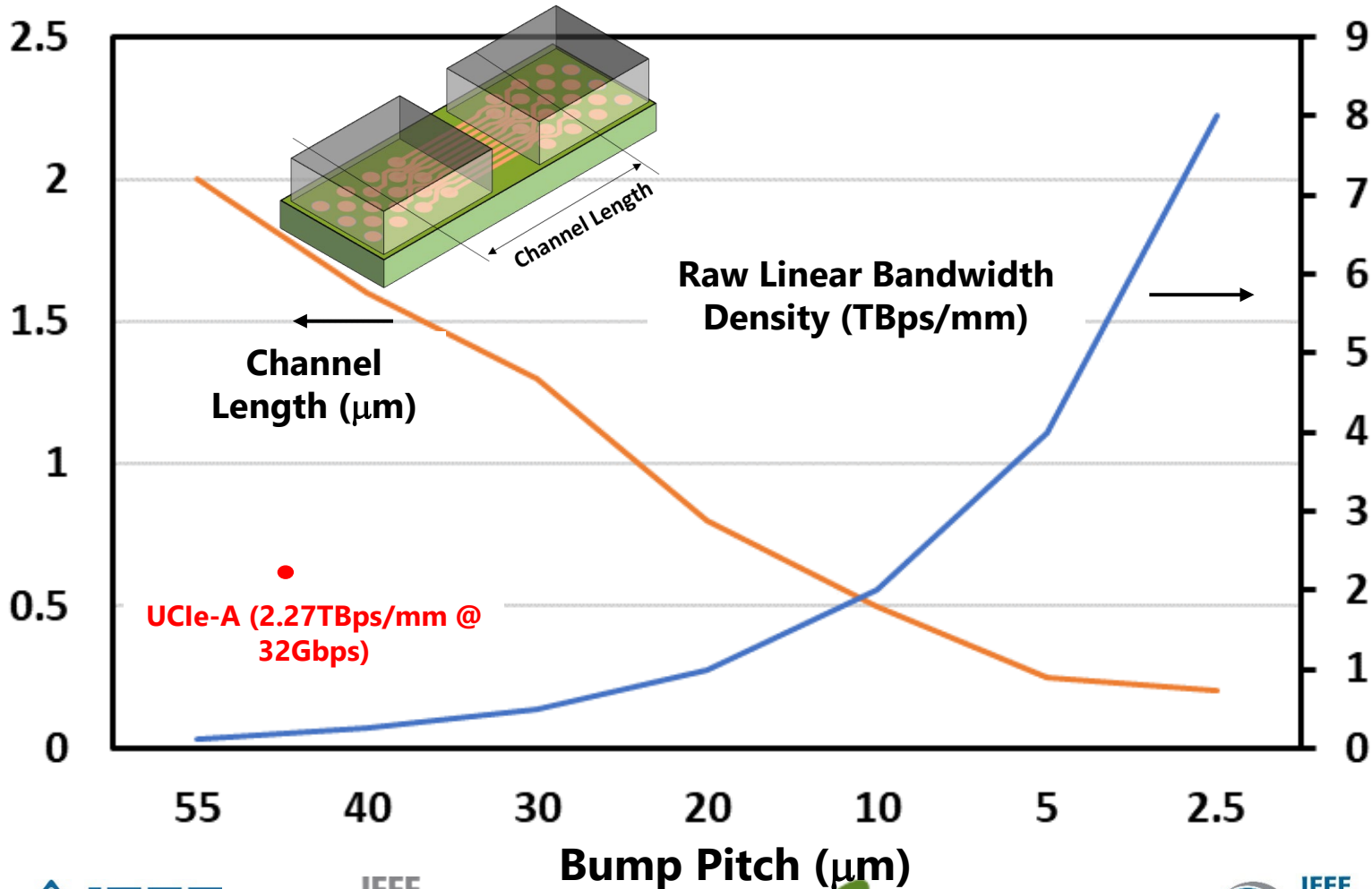
- **Die-Die Interconnects:** Interconnects between stacked die that enable vertical interconnects between multiple die in a 3-D stack *Covered in this chapter*
- **On-package Die-Die Interconnects** i.e., 2D and Enhanced 2D Interconnects: Interconnects between die within the package that enable lateral connections *Covered in this chapter*
- **Die-to-Package (*or to substrate*) Interconnects:** Interconnects between the die and the package typically known as the first level interconnect (FLI) *Covered in this chapter*
- **Within Package Interconnects:** Interconnects within the package that enable lateral connections *Covered in the Substrate Section of the Single Chip and Multi-Chip Chapter*
- **Package to Board Interconnects:** Interconnects between the package and the next level, which is typically the motherboard, referred to as the second level interconnect (SLI) *Covered in this chapter*
- **Package on Package Interconnects** *Covered in this chapter*

Nomenclature



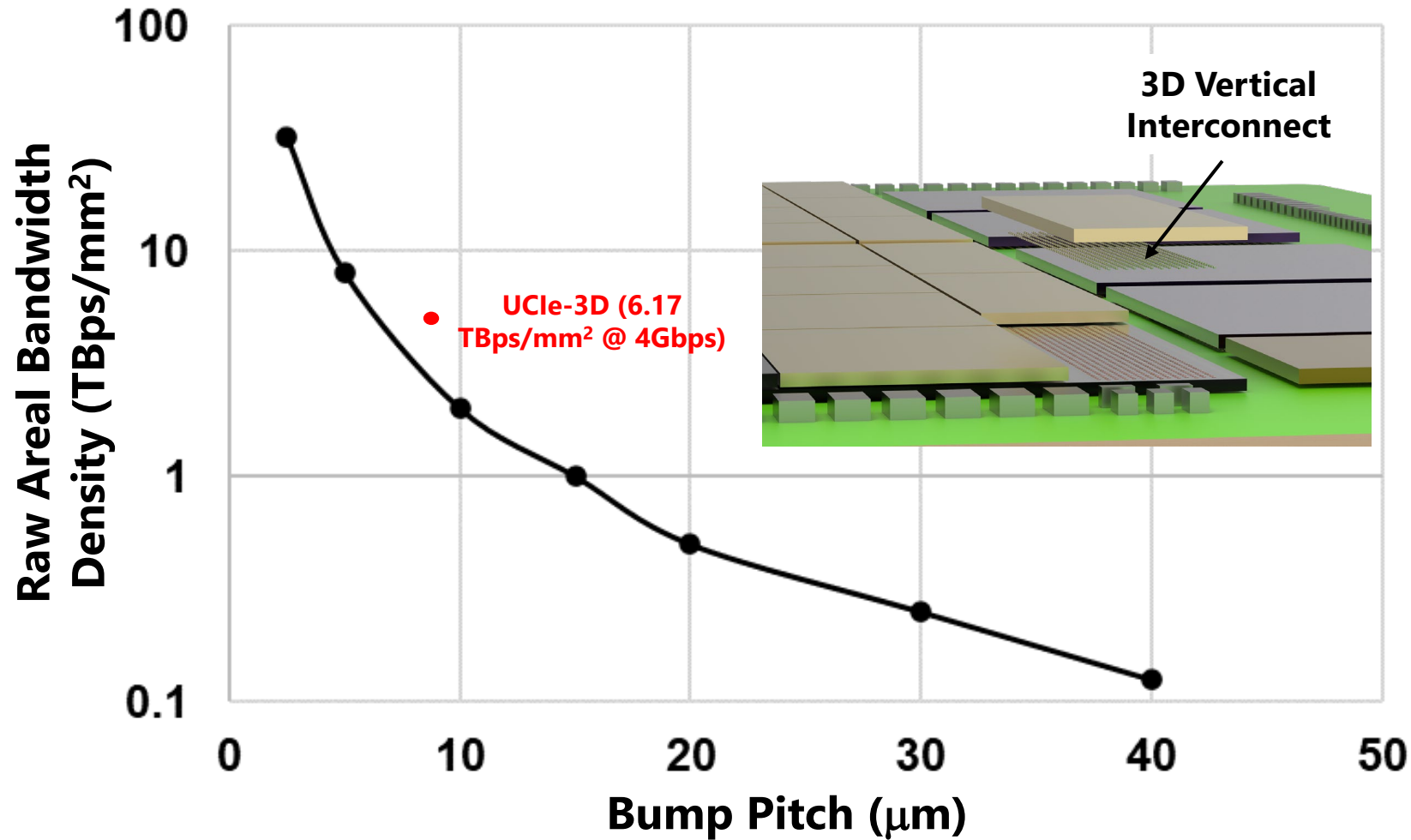
- Add Chip-Mid & Improve Picture (Ref: D. C. Hu et al., "2.2D Die last Integrated Substrate for High Performance Applications," 2021 IEEE 71st Electronic Components and Technology Conference (ECTC), San Diego, CA, USA, 2021, pp. 157-163)
- Clarify 2DO includes organic interposers
- Add a broader interconnect hierarchy picture

Non-Unique On-Package Planar Interconnect Scaling Roadmap



- @ 32Gbps UCle-A theoretical BW@ 45µm pitch is 2.2716 TBps & this roadmap states @ 3Gbps & @ 40µm pitch a theoretical BW of 0.25TBps is possible. There is no discrepancy in the numbers and modulating speed (hence power efficiency) is a knob for scaling BW → lots of room to grow
- Extended to 7 generations

On-Package 3D Interconnect Scaling Roadmap



- Extended to 8 generations
- Signaling speed ≤ 1.8 Gbps (speed is a knob \rightarrow room to grow)

Signal Integrity Attributes

Generation Number →		1	2	3	4	5	6	7
Linear Bandwidth Density (GBps/mm)		125	250	500	1000	2000	4000	8000
Channel Performance	Channel Length (mm)	<2.0	<1.7	<1.4	<0.8	<0.50	<0.25	<0.15
	Bump-to-Bump Channel RC (ps)	<10	<10	<10	<10	<10	<10	<10

Channel Signaling Characteristics for 2D and Enhanced-2D Architectures (RC Dominated)

Generation Number →			1	2	3	4	5	6	7	8
Areal Bandwidth Density	(GBps/mm ²)		125	250	500	1000	2000	8000	32000	200000
Bump Capacitance (fF)			<30	<22	<15	<10	<7	<5	<3	<1

Channel Signaling Characteristics for 3D Architectures (Capacitance Dominated)

Power Delivery Attributes: Area Interconnects for 2D and 3D Architectures

Year	2024	2026	2028	2030	2032
Maximum Core Power Density (W/mm ²)	5	7	10	14	20
Sustained Core Power Density (W/mm ²)	1	1.4	2	2.8	4
On-die MIM Capacitance Density (nF/mm ²)	140	210	320	520	800
VR Power Density (W/mm ²)	1	1.4	2	2.8	4
Ceramic Cap Density (μF/mm ²)	10	14	20	28	40
Sustained Bump Current Carrying Capability (A/mm ²)	1.4	2.1	3.2	5.2	8

Power delivery Attributes for 2D, Enhanced-2D and 3D Architectures. It should be noted that power delivery attributes are agnostic to the architecture

Cross-TWVG Collaboration Opportunities

- Substrates and Power Delivery are key areas of Interaction
- This chapter (with appropriate calibration) should be the basis of driving on-package signaling definition



Back-up



Metrology Focus Areas*

- Characterization Metrologies for Model development and Validation
 - Warpage as a function of temperature
 - Properties (Mechanical, Thermal, Electrical, Interface)
- In-Situ (Fast & Accurate) Process Metrologies
 - Defects (Voids, Cracks, Delamination, Residue)
 - Dimensional metrologies
- Reliability
 - Defects (Voids, Cracks, Delamination, Residue)
 - FA/FI Techniques/Enablers

* Partial List. See refs (e.g., SRC Needs (<https://www.src.org/program/grc/research-needs/>)) for a more detailed discussion